

2CLG3508 2CLG3508(T)

High Voltage Diodes for Micro-wave Oven

■ Features

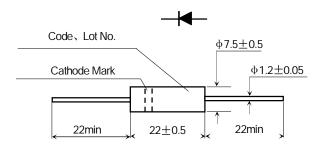
High reliability

■ Applications

 Rectification for high voltage power supply of magnetron in Micro wave oven and others

■ Outline Dimensions and Mark

Unit: mm



Туре	Code	Cathode Mark
2CLG3508	TG3508	
2CLG3508(T)	TG3508	

■Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	9/	2CLG3508	2CLG3508(T)
Repetitive Peak Reverse Voltage	V_{RRM}	kV		7.5	8
Average Forward Current	I _{F(AV)}	mA	350	(50HzHalf-sine wave, Resistance load, Ta \leq 60 $^{\circ}$ C)	
Forward Surge Current	I _{FSM}	А	15	(50HZ Half-sine wave, One-shot, Ta=25°ℂ)	
Reverse Surge Current	I _{RSM}	mA	50	(W _P =1ms, Rectangular-wave, One-shot, T _a =25°C)	
virtual Junction Temperature	T _(vj)	$^{\circ}$		120	
Storage Temperature	T _{stg}	$^{\circ}$	-40 ~ +130		

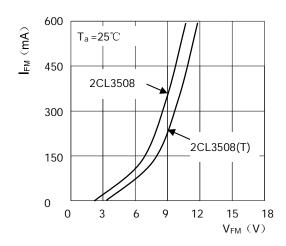
^{*}Cooling Requirement: Cathode terminal is fastened to radiating fin that size is more than 50mm×50mm×0.6mm Wind-cooled velocity is more than 0.5m/s

■ Electrical Characteristics (T_a=25°C Unless otherwise specified)

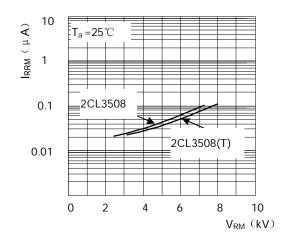
Item	Symbol	Unit	Test Condition	2CLG3508	2CLG3508(T)	
Peak Forward Voltage	V_{FM}	>	I _{FM} =350mA	≤13.5	≤14.0	
Peak Reverse Current	I _{RRM1}	μA	$V_{RM} = V_{RRM}$	≤10		
Rererse Recovery Time	trr	μs	I _F =100mA, I _R =100mA 90% Recover	≤0.15		
Avalanche Breakdown Voltage	V (BR)	kV	I _R =100 μ A	<i>≥</i> 7.6	≥8.5	

Power Semiconductor Technology

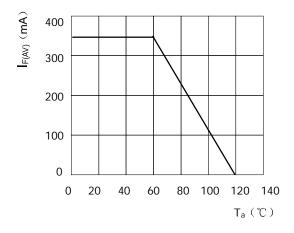
■ Characteristics(Typical)



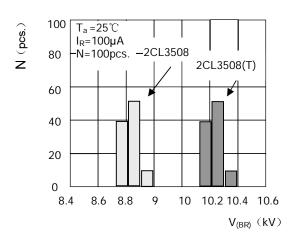
Forward Characteristics



Reverse Characteristics

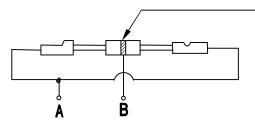


I_{F (AV)} —T_a Derating



Breakdown Voltage Distribution

Safety Test



1.Insulation Resistance Test:500V DC voltage is added between A and B. The measurement by insulation resistance meter is big than 1000M Ω .

3mm Wide metal film is rolled on the surface middle of diode body

 Resistance To Voltage Strength Test: 15kV halfsine wave voltage is added between A and B for one minute and no breakdown or arc in insulation oil.